AMD Xilinx - XA3S500E-4FTG256I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	1164
Number of Logic Elements/Cells	10476
Total RAM Bits	368640
Number of I/O	190
Number of Gates	500000
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xa3s500e-4ftg256i

Key Feature Differences from Commercial XC Devices

- AEC-Q100 device qualification and full production part approval process (PPAP) documentation support available in both extended temperature I- and Q-Grades
- Guaranteed to meet full electrical specification over the T_J = –40°C to +125°C temperature range (Q-Grade)
- XA Spartan-3E devices are available in the -4 speed grade only.
- PCI-66 is not supported in the XA Spartan-3E FPGA product line.
- The readback feature is not supported in the XA Spartan-3E FPGA product line.
- XA Spartan-3E devices are available in Step 1 only.
- JTAG configuration frequency reduced from 30 MHz to 25 MHz.
- Platform Flash is not supported within the XA family.
- XA Spartan-3E devices are available in Pb-free packaging only.
- MultiBoot is not supported in XA versions of this product.
- The XA Spartan-3E device must be power cycled prior to reconfiguration.

Table 1: **Summary of XA Spartan-3E FPGA Attributes**

Device	System Gates	Equivalent Logic Cells	CLB Array (One CLB = Four Slices)				Distributed RAM bits(1)	Block RAM bits(1)	Dedicated Multipliers	DCMs	Maximum User I/O	Maximum Differential I/O Pairs
			Rows	Columns	Total CLBs	Total Slices						
XA3S100E	100K	2,160	22	16	240	960	15K	72K	4	2	108	40
XA3S250E	250K	5,508	34	26	612	2,448	38K	216K	12	4	172	68
XA3S500E	500K	10,476	46	34	1,164	4,656	73K	360K	20	4	190	77
XA3S1200E	1200K	19,512	60	46	2,168	8,672	136K	504K	28	8	304	124
XA3S1600E	1600K	33,192	76	58	3,688	14,752	231K	648K	36	8	376	156

Notes:

1. By convention, one Kb is equivalent to 1,024 bits.

Architectural Overview

The XA Spartan-3E family architecture consists of five fundamental programmable functional elements:

- **Configurable Logic Blocks (CLBs)** contain flexible Look-Up Tables (LUTs) that implement logic plus storage elements used as flip-flops or latches. CLBs perform a wide variety of logical functions as well as store data.
- **Input/Output Blocks (IOBs)** control the flow of data between the I/O pins and the internal logic of the device. Each IOB supports bidirectional data flow plus 3-state operation. Supports a variety of signal standards, including four high-performance differential standards. Double Data-Rate (DDR) registers are included.
- **Block RAM** provides data storage in the form of 18-Kbit dual-port blocks.
- **Multiplier Blocks** accept two 18-bit binary numbers as inputs and calculate the product.
- **Digital Clock Manager (DCM) Blocks** provide self-calibrating, fully digital solutions for distributing, delaying, multiplying, dividing, and phase-shifting clock signals.

These elements are organized as shown in Figure 1. A ring of IOBs surrounds a regular array of CLBs. Each device has two columns of block RAM except for the XA3S100E, which has one column. Each RAM column consists of several 18-Kbit RAM blocks. Each block RAM is associated with a dedicated multiplier. The DCMs are positioned in the center with two at the top and two at the bottom of the device. The XA3S100E has only one DCM at the top and bottom, while the XA3S1200E and XA3S1600E add two DCMs in the middle of the left and right sides.

The XA Spartan-3E family features a rich network of traces that interconnect all five functional elements, transmitting signals among them. Each functional element has an associated switch matrix that permits multiple connections to the routing.

Package Marking

Figure 2 provides a top marking example for XA Spartan-3E FPGAs in the quad-flat packages. Figure 3 shows the top marking for XA Spartan-3E FPGAs in BGA packages except the 132-ball chip-scale package (CPG132). The markings for the BGA packages are nearly identical to those for the quad-flat packages, except that the marking is rotated with respect to the ball A1 indicator. Figure 4 shows the top marking for XA Spartan-3E FPGAs in the CPG132 package.

Note: **No marking is shown for stepping.**

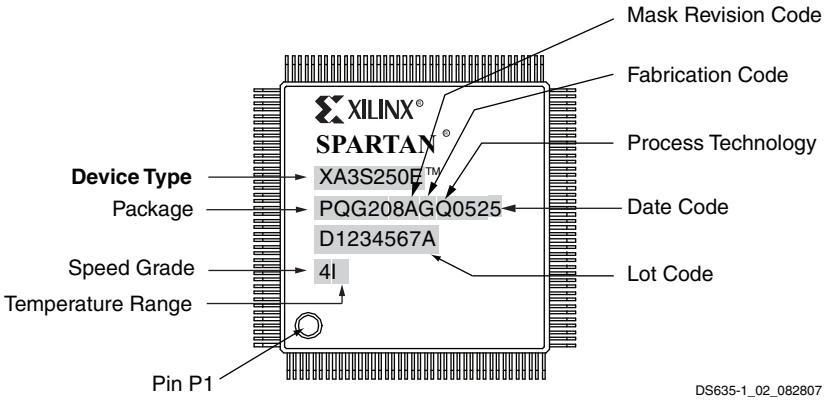

Figure 2: **XA Spartan-3E FPGA QFP Package Marking Example**

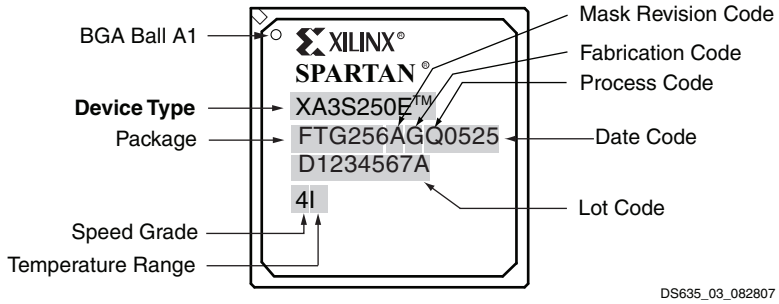

Figure 3: **XA Spartan-3E FPGA BGA Package Marking Example**

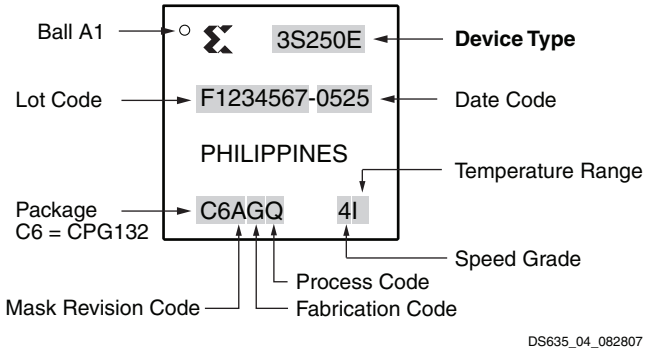

Figure 4: **XA Spartan-3E FPGA CPG132 Package Marking Example**

DC Specifications

Table 6: **General Recommended Operating Conditions**

Symbol	Description		Min	Nominal	Max	Units
T_J	Junction temperature	I-Grade	–40	25	100	°C
		Q-Grade	–40	25	125	°C
V_{CCINT}	Internal supply voltage		1.140	1.200	1.260	V
V_{CCO}(1)	Output driver supply voltage		1.100	-	3.465	V
V_{CCAUX}	Auxiliary supply voltage		2.375	2.500	2.625	V
ΔV_{CCAUX}(2)	Voltage variance on V_{CCAUX} when using a DCM		-	-	10	mV/ms
V_{IN}(3,4,5,6)	Input voltage extremes to avoid turning on I/O protection diodes	I/O, Input-only, and Dual-Purpose pins(3)	–0.5	–	V_{CCO} + 0.5	V
		Dedicated pins(4)	–0.5	–	V_{CCAUX} + 0.5	V
T_{IN}	Input signal transition time(7)		–	–	500	ns

Notes:

1. This V_{CCO} range spans the lowest and highest operating voltages for all supported I/O standards. Table 9 lists the recommended V_{CCO} range specific to each of the single-ended I/O standards, and Table 11 lists that specific to the differential standards.
2. Only during DCM operation is it recommended that the rate of change of V_{CCAUX} not exceed 10 mV/ms.
3. Each of the User I/O and Dual-Purpose pins is associated with one of the four banks' V_{CCO} rails. Meeting the V_{IN} limit ensures that the internal diode junctions that exist between these pins and their associated V_{CCO} and GND rails do not turn on. See Absolute Maximum Ratings in DS312).
4. All Dedicated pins (PROG_B, DONE, TCK, TDI, TDO, and TMS) draw power from the V_{CCAUX} rail (2.5V). Meeting the V_{IN} max limit ensures that the internal diode junctions that exist between each of these pins and the V_{CCAUX} and GND rails do not turn on.
5. Input voltages outside the recommended range is permissible provided that the I_{IK} input clamp diode rating is met and no more than 100 pins exceed the range simultaneously. See Absolute Maximum Ratings in DS312).
6. See XAPP459, "Eliminating I/O Coupling Effects when Interfacing Large-Swing Single-Ended Signals to User I/O Pins."
7. Measured between 10% and 90% V_{CCO}. Follow Signal Integrity recommendations.

General DC Characteristics for I/O Pins

Table 7: **General DC Characteristics of User I/O, Dual-Purpose, and Dedicated Pins**

Symbol	Description	Test Conditions	Min	Typ	Max	Units
I_L	Leakage current at User I/O, Input-only, Dual-Purpose, and Dedicated pins	Driver is in a high-impedance state, V_{IN} = 0V or V_{CCO} max, sample-tested	–10	–	+10	µA
I_{RPU}(2)	Current through pull-up resistor at User I/O, Dual-Purpose, Input-only, and Dedicated pins	V_{IN} = 0V, V_{CCO} = 3.3V	–0.36	–	–1.24	mA
		V_{IN} = 0V, V_{CCO} = 2.5V	–0.22	–	–0.80	mA
		V_{IN} = 0V, V_{CCO} = 1.8V	–0.10	–	–0.42	mA
		V_{IN} = 0V, V_{CCO} = 1.5V	–0.06	–	–0.27	mA
		V_{IN} = 0V, V_{CCO} = 1.2V	–0.04	–	–0.22	mA
R_{PU}(2)	Equivalent pull-up resistor value at User I/O, Dual-Purpose, Input-only, and Dedicated pins (based on I_{RPU} per Note 2)	V_{IN} = 0V, V_{CCO} = 3.0V to 3.465V	2.4	–	10.8	kΩ
		V_{IN} = 0V, V_{CCO} = 2.3V to 2.7V	2.7	–	11.8	kΩ
		V_{IN} = 0V, V_{CCO} = 1.7V to 1.9V	4.3	–	20.2	kΩ
		V_{IN} = 0V, V_{CCO} =1.4V to 1.6V	5.0	–	25.9	kΩ
		V_{IN} = 0V, V_{CCO} = 1.14V to 1.26V	5.5	–	32.0	kΩ

Table 7: **General DC Characteristics of User I/O, Dual-Purpose, and Dedicated Pins *(Continued)***

Symbol	Description	Test Conditions	Min	Typ	Max	Units
I_{RPD}(2)	Current through pull-down resistor at User I/O, Dual-Purpose, Input-only, and Dedicated pins	$V_{IN} = V_{CCO}$	0.10	–	0.75	mA
R_{PD}(2)	Equivalent pull-down resistor value at User I/O, Dual-Purpose, Input-only, and Dedicated pins (based on I_{RPD} per Note 2)	$V_{IN} = V_{CCO}$ = 3.0V to 3.45V	4.0	–	34.5	kΩ
		$V_{IN} = V_{CCO}$ = 2.3V to 2.7V	3.0	–	27.0	kΩ
		$V_{IN} = V_{CCO}$ = 1.7V to 1.9V	2.3	–	19.0	kΩ
		$V_{IN} = V_{CCO}$ = 1.4V to 1.6V	1.8	–	16.0	kΩ
		$V_{IN} = V_{CCO}$ = 1.14V to 1.26V	1.5	–	12.6	kΩ
I_{REF}	V_{REF} current per pin	All V_{CCO} levels	–10	–	+10	µA
C_{IN}	Input capacitance	-	–	–	10	pF
R_{DT}	Resistance of optional differential termination circuit within a differential I/O pair. Not available on Input-only pairs.	V_{OCM} Min ≤ V_{ICM} ≤ V_{OCM} Max V_{OD} Min ≤ V_{ID} ≤ V_{OD} Max V_{CCO} = 2.5V	–	120	–	Ω

Notes:

1. The numbers in this table are based on the conditions set forth in Table 6.
2. This parameter is based on characterization. The pull-up resistance $R_{PU} = V_{CCO} / I_{RPU}$. The pull-down resistance $R_{PD} = V_{IN} / I_{RPD}$.

Table 8: **Quiescent Supply Current Characteristics**

Symbol	Description	Device	I-Grade Maximum	Q-Grade Maximum	Units
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XA3S100E	36	58	mA
		XA3S250E	104	158	mA
		XA3S500E	145	300	mA
		XA3S1200E	324	500	mA
		XA3S1600E	457	750	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XA3S100E	1.5	2.0	mA
		XA3S250E	1.5	3.0	mA
		XA3S500E	1.5	3.0	mA
		XA3S1200E	2.5	4.0	mA
		XA3S1600E	2.5	4.0	mA

Table 8: **Quiescent Supply Current Characteristics *(Continued)***

Symbol	Description	Device	I-Grade Maximum	Q-Grade Maximum	Units
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XA3S100E	13	22	mA
		XA3S250E	26	43	mA
		XA3S500E	34	63	mA
		XA3S1200E	59	100	mA
		XA3S1600E	86	150	mA

Notes:

1. The numbers in this table are based on the conditions set forth in Table 6.
2. Quiescent supply current is measured with all I/O drivers in a high-impedance state and with all pull-up/pull-down resistors at the I/O pads disabled. Typical values are characterized using typical devices at room temperature (T_J of 25°C at V_{CCINT} = 1.2 V, V_{CCO} = 3.3V, and V_{CCAUX} = 2.5V). The maximum limits are tested for each device at the respective maximum specified junction temperature and at maximum voltage limits with V_{CCINT} = 1.26V, V_{CCO} = 3.465V, and V_{CCAUX} = 2.625V. The FPGA is programmed with a "blank" configuration data file (i.e., a design with no functional elements instantiated). For conditions other than those described above, (e.g., a design including functional elements), measured quiescent current levels may be different than the values in the table. For more accurate estimates for a specific design, use the Xilinx XPower tools.
3. There are two recommended ways to estimate the total power consumption (quiescent plus dynamic) for a specific design: a) The Spartan-3E XPower Estimator provides quick, approximate, typical estimates, and does not require a netlist of the design. b) XPower Analyzer uses a netlist as input to provide maximum estimates as well as more accurate typical estimates.
4. The maximum numbers in this table indicate the minimum current each power rail requires in order for the FPGA to power-on successfully.

Table 14: **Pin-to-Pin Setup and Hold Times for the IOB Input Path (System Synchronous)**

Symbol	Description	Conditions	IFD_DELAY_VALUE=	Device	-4 Speed Grade	Units
					Min	
Setup Times						
T_{PSDCM}	When writing to the Input Flip-Flop (IFF), the time from the setup of data at the Input pin to the active transition at a Global Clock pin. The DCM is used. No Input Delay is programmed.	LVCMOS25(2), IFD_DELAY_VALUE = 0, with DCM(4)	0	**XA3S100E**	2.98	ns
				XA3S250E	2.59	ns
				XA3S500E	2.59	ns
				XA3S1200E	2.58	ns
				XA3S1600E	2.59	ns
T_{PSFD}	When writing to IFF, the time from the setup of data at the Input pin to an active transition at the Global Clock pin. The DCM is not used. The Input Delay is programmed.	LVCMOS25(2), IFD_DELAY_VALUE = default software setting	2	**XA3S100E**	3.58	ns
			3	**XA3S250E**	3.91	ns
			2	**XA3S500E**	4.02	ns
			5	**XA3S1200E**	5.52	ns
			4	**XA3S1600E**	4.46	ns
Hold Times						
T_{PHDCM}	When writing to IFF, the time from the active transition at the Global Clock pin to the point when data must be held at the Input pin. The DCM is used. No Input Delay is programmed.	LVCMOS25(3), IFD_DELAY_VALUE = 0, with DCM(4)	0	**XA3S100E**	–0.52	ns
				XA3S250E	0.14	ns
				XA3S500E	0.14	ns
				XA3S1200E	0.15	ns
				XA3S1600E	0.14	ns
T_{PHFD}	When writing to IFF, the time from the active transition at the Global Clock pin to the point when data must be held at the Input pin. The DCM is not used. The Input Delay is programmed.	LVCMOS25(3), IFD_DELAY_VALUE = default software setting	2	**XA3S100E**	–0.24	ns
			3	**XA3S250E**	–0.32	ns
			2	**XA3S500E**	–0.49	ns
			5	**XA3S1200E**	–0.63	ns
			4	**XA3S1600E**	–0.39	ns

Notes:

1. The numbers in this table are tested using the methodology presented in Table 19 and are based on the operating conditions set forth in Table 6 and Table 9.
2. This setup time requires adjustment whenever a signal standard other than LVCMOS25 is assigned to the Global Clock Input or the data Input. If this is true of the Global Clock Input, subtract the appropriate adjustment from Table 17. If this is true of the data Input, add the appropriate Input adjustment from the same table.
3. This hold time requires adjustment whenever a signal standard other than LVCMOS25 is assigned to the Global Clock Input or the data Input. If this is true of the Global Clock Input, add the appropriate Input adjustment from Table 17. If this is true of the data Input, subtract the appropriate Input adjustment from the same table. When the hold time is negative, it is possible to change the data before the clock's active edge.
4. DCM output jitter is included in all measurements.

Table 19: **Test Methods for Timing Measurement at I/Os**

Signal Standard (IOSTANDARD)		Inputs			Outputs		Inputs and Outputs
		V_{REF} (V)	V_L (V)	V_H (V)	R_T (Ω)	V_T (V)	V_M (V)
Single-Ended							
LVTTL		-	0	3.3	1M	0	1.4
LVCMOS33		-	0	3.3	1M	0	1.65
LVCMOS25		-	0	2.5	1M	0	1.25
LVCMOS18		-	0	1.8	1M	0	0.9
LVCMOS15		-	0	1.5	1M	0	0.75
LVCMOS12		-	0	1.2	1M	0	0.6
PCI33_3	Rising	-	Note 3	Note 3	25	0	0.94
	Falling				25	3.3	2.03
HSTL_I_18		0.9	V_{REF} – 0.5	V_{REF} + 0.5	50	0.9	V_{REF}
HSTL_III_18		1.1	V_{REF} – 0.5	V_{REF} + 0.5	50	1.8	V_{REF}
SSTL18_I		0.9	V_{REF} – 0.5	V_{REF} + 0.5	50	0.9	V_{REF}
SSTL2_I		1.25	V_{REF} – 0.75	V_{REF} + 0.75	50	1.25	V_{REF}
Differential							
LVDS_25		-	V_{ICM} – 0.125	V_{ICM} + 0.125	50	1.2	V_{ICM}
BLVDS_25		-	V_{ICM} – 0.125	V_{ICM} + 0.125	1M	0	V_{ICM}
MINI_LVDS_25		-	V_{ICM} – 0.125	V_{ICM} + 0.125	50	1.2	V_{ICM}
LVPECL_25		-	V_{ICM} – 0.3	V_{ICM} + 0.3	1M	0	V_{ICM}
RSDS_25		-	V_{ICM} – 0.1	V_{ICM} + 0.1	50	1.2	V_{ICM}
DIFF_HSTL_I_18		-	V_{REF} – 0.5	V_{REF} + 0.5	50	0.9	V_{ICM}
DIFF_HSTL_III_18		-	V_{REF} – 0.5	V_{REF} + 0.5	50	1.8	V_{ICM}
DIFF_SSTL18_I		-	V_{REF} – 0.5	V_{REF} + 0.5	50	0.9	V_{ICM}
DIFF_SSTL2_I		-	V_{REF} – 0.5	V_{REF} + 0.5	50	1.25	V_{ICM}

Notes:

1. Descriptions of the relevant symbols are as follows:
   V_{REF} – The reference voltage for setting the input switching threshold
   V_{ICM} – The common mode input voltage
   V_M – Voltage of measurement point on signal transition
   V_L – Low-level test voltage at Input pin
   V_H – High-level test voltage at Input pin
   R_T – Effective termination resistance, which takes on a value of 1MΩ when no parallel termination is required
   V_T – Termination voltage
2. The load capacitance (C_L) at the Output pin is 0 pF for all signal standards.
3. According to the PCI specification.

Configurable Logic Block Timing

Table 20: **CLB (SLICEM) Timing**

Symbol	Description	-4 Speed Grade		Units
		Min	Max	
Clock-to-Output Times				
T_{CKO}	When reading from the FFX (FFY) Flip-Flop, the time from the active transition at the CLK input to data appearing at the XQ (YQ) output	-	0.60	ns
Setup Times				
T_{AS}	Time from the setup of data at the F or G input to the active transition at the CLK input of the CLB	0.52	-	ns
T_{DICK}	Time from the setup of data at the BX or BY input to the active transition at the CLK input of the CLB	1.81	-	ns
Hold Times				
T_{AH}	Time from the active transition at the CLK input to the point where data is last held at the F or G input	0	-	ns
T_{CKDI}	Time from the active transition at the CLK input to the point where data is last held at the BX or BY input	0	-	ns
Clock Timing				
T_{CH}	The High pulse width of the CLB's CLK signal	0.80	-	ns
T_{CL}	The Low pulse width of the CLK signal	0.80	-	ns
F_{TOG}	Toggle frequency (for export control)	0	572	MHz
Propagation Times				
T_{ILO}	The time it takes for data to travel from the CLB's F (G) input to the X (Y) output	-	0.76	ns
Set/Reset Pulse Width				
T_{RPW_CLB}	The minimum allowable pulse width, High or Low, to the CLB's SR input	1.80	-	ns

Notes:

1. The numbers in this table are based on the operating conditions set forth in Table 6.

Table 21: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	-4		Units
		Min	Max	
Clock-to-Output Times				
T_{SHCKO}	Time from the active edge at the CLK input to data appearing on the distributed RAM output	-	2.35	ns
Setup Times				
T_{DS}	Setup time of data at the BX or BY input before the active transition at the CLK input of the distributed RAM	0.46	-	ns
T_{AS}	Setup time of the F/G address inputs before the active transition at the CLK input of the distributed RAM	0.52	-	ns
T_{WS}	Setup time of the write enable input before the active transition at the CLK input of the distributed RAM	0.40	-	ns
Hold Times				
T_{DH}	Hold time of the BX, BY data inputs after the active transition at the CLK input of the distributed RAM	0.15	-	ns
T_{AH}, T_{WH}	Hold time of the F/G address inputs or the write enable input after the active transition at the CLK input of the distributed RAM	0	-	ns
Clock Pulse Width				
T_{WPH}, T_{WPL}	Minimum High or Low pulse width at CLK input	1.01	-	ns

Table 22: **CLB Shift Register Switching Characteristics**

Symbol	Description	-4		Units
		Min	Max	
Clock-to-Output Times				
T_{REG}	Time from the active edge at the CLK input to data appearing on the shift register output	-	4.16	ns
Setup Times				
T_{SRLDS}	Setup time of data at the BX or BY input before the active transition at the CLK input of the shift register	0.46	-	ns
Hold Times				
T_{SRLDH}	Hold time of the BX or BY data input after the active transition at the CLK input of the shift register	0.16	-	ns
Clock Pulse Width				
T_{WPH}, T_{WPL}	Minimum High or Low pulse width at CLK input	1.01	-	ns

Clock Buffer/Multiplexer Switching Characteristics

Table 23: **Clock Distribution Switching Characteristics**

Description	Symbol	Maximum	Units
		-4 Speed Grade	
Global clock buffer (BUFG, BUFGMUX, BUFGCE) I input to O-output delay	T_{GIO}	1.46	ns
Global clock multiplexer (BUFGMUX) select S-input setup to I0 and I1 inputs. Same as BUFGCE enable CE-input	T_{GSI}	0.63	ns
Frequency of signals distributed on global buffers (all sides)	F_{BUFG}	311	MHz

18 x 18 Embedded Multiplier Timing

Table 24: **18 x 18 Embedded Multiplier Timing**

Symbol	Description	-4 Speed Grade		Units
		Min	Max	
Combinatorial Delay				
T_{MULT}	Combinatorial multiplier propagation delay from the A and B inputs to the P outputs, assuming 18-bit inputs and a 36-bit product (AREG, BREG, and PREG registers unused)	-	4.88(1)	ns
Clock-to-Output Times				
T_{MSCKP_P}	Clock-to-output delay from the active transition of the CLK input to valid data appearing on the P outputs when using the PREG register(2)	-	1.10	ns
T_{MSCKP_A} T_{MSCKP_B}	Clock-to-output delay from the active transition of the CLK input to valid data appearing on the P outputs when using either the AREG or BREG register(3)	-	4.97	ns
Setup Times				
T_{MSDCK_P}	Data setup time at the A or B input before the active transition at the CLK when using only the PREG output register (AREG, BREG registers unused)(2)	3.98	-	ns
T_{MSDCK_A}	Data setup time at the A input before the active transition at the CLK when using the AREG input register(3)	0.23	-	ns
T_{MSDCK_B}	Data setup time at the B input before the active transition at the CLK when using the BREG input register(3)	0.39	-	ns
Hold Times				
T_{MSCKD_P}	Data hold time at the A or B input before the active transition at the CLK when using only the PREG output register (AREG, BREG registers unused)(2)	-0.97		
T_{MSCKD_A}	Data hold time at the A input before the active transition at the CLK when using the AREG input register(3)	0.04		
T_{MSCKD_B}	Data hold time at the B input before the active transition at the CLK when using the BREG input register(3)	0.05		

Table 24: **18 x 18 Embedded Multiplier Timing *(Continued)***

Symbol	Description	-4 Speed Grade		Units
		Min	Max	
Clock Frequency				
F_{MULT}	Internal operating frequency for a two-stage 18x18 multiplier using the AREG and BREG input registers and the PREG output register(1)	0	240	MHz

Notes:

1. Combinatorial delay is less and pipelined performance is higher when multiplying input data with less than 18 bits.
2. The PREG register is typically used in both single-stage and two-stage pipelined multiplier implementations.
3. Input registers AREG or BREG are typically used when inferring a two-stage multiplier.

Block RAM Timing

Table 25: **Block RAM Timing**

Symbol	Description	-4 Speed Grade		Units
		Min	Max	
Clock-to-Output Times				
T_{BCKO}	When reading from block RAM, the delay from the active transition at the CLK input to data appearing at the DOUT output	-	2.82	ns
Setup Times				
T_{BACK}	Setup time for the ADDR inputs before the active transition at the CLK input of the block RAM	0.38	-	ns
T_{BDCK}	Setup time for data at the DIN inputs before the active transition at the CLK input of the block RAM	0.23	-	ns
T_{BECK}	Setup time for the EN input before the active transition at the CLK input of the block RAM	0.77	-	ns
T_{BWCK}	Setup time for the WE input before the active transition at the CLK input of the block RAM	1.26	-	ns
Hold Times				
T_{BCKA}	Hold time on the ADDR inputs after the active transition at the CLK input	0.14	-	ns
T_{BCKD}	Hold time on the DIN inputs after the active transition at the CLK input	0.13	-	ns
T_{BCKE}	Hold time on the EN input after the active transition at the CLK input	0	-	ns
T_{BCKW}	Hold time on the WE input after the active transition at the CLK input	0	-	ns

Delay-Locked Loop

Table 26: **Recommended Operating Conditions for the DLL**

Symbol		Description		-4 Speed Grade		Units
				Min	Max	
Input Frequency Ranges						
F_{CLKIN}	CLKIN_FREQ_DLL	Frequency of the CLKIN clock input		5(2)	240(3)	MHz
Input Pulse Requirements						
CLKIN_PULSE		CLKIN pulse width as a percentage of the CLKIN period	$F_{CLKIN} \le 150$ MHz	40%	60%	-
			$F_{CLKIN} > 150$ MHz	45%	55%	-
Input Clock Jitter Tolerance and Delay Path Variation(4)						
CLKIN_CYC_JITT_DLL_LF		Cycle-to-cycle jitter at the CLKIN input	$F_{CLKIN} \le 150$ MHz	-	±300	ps
CLKIN_CYC_JITT_DLL_HF			$F_{CLKIN} > 150$ MHz	-	±150	ps
CLKIN_PER_JITT_DLL		Period jitter at the CLKIN input		-	±1	ns
CLKFB_DELAY_VAR_EXT		Allowable variation of off-chip feedback delay from the DCM output to the CLKFB input		-	±1	ns

Notes:

1. DLL specifications apply when any of the DLL outputs (CLK0, CLK90, CLK180, CLK270, CLK2X, CLK2X180, or CLKDV) are in use.
2. The DFS, when operating independently of the DLL, supports lower FCLKIN frequencies. See Table 28.
3. To support double the maximum effective FCLKIN limit, set the CLKIN_DIVIDE_BY_2 attribute to TRUE. This attribute divides the incoming clock frequency by two as it enters the DCM. The CLK2X output reproduces the clock frequency provided on the CLKIN input.
4. CLKIN input jitter beyond these limits might cause the DCM to lose lock.

Table 27: **Switching Characteristics for the DLL**

Symbol	Description	-4 Speed Grade		Units
		Min	Max	
Output Frequency Ranges				
CLKOUT_FREQ_CLK0	Frequency for the CLK0 and CLK180 outputs	5	240	MHz
CLKOUT_FREQ_CLK90	Frequency for the CLK90 and CLK270 outputs	5	200	MHz
CLKOUT_FREQ_2X	Frequency for the CLK2X and CLK2X180 outputs	10	311	MHz
CLKOUT_FREQ_DV	Frequency for the CLKDV output	0.3125	160	MHz
Output Clock Jitter(2,3,4)				
CLKOUT_PER_JITT_0	Period jitter at the CLK0 output	-	±100	ps
CLKOUT_PER_JITT_90	Period jitter at the CLK90 output	-	±150	ps
CLKOUT_PER_JITT_180	Period jitter at the CLK180 output	-	±150	ps
CLKOUT_PER_JITT_270	Period jitter at the CLK270 output	-	±150	ps
CLKOUT_PER_JITT_2X	Period jitter at the CLK2X and CLK2X180 outputs	-	±[1% of CLKIN period + 150]	ps
CLKOUT_PER_JITT_DV1	Period jitter at the CLKDV output when performing integer division	-	±150	ps
CLKOUT_PER_JITT_DV2	Period jitter at the CLKDV output when performing non-integer division	-	±[1% of CLKIN period + 200]	ps

Table 31: **Switching Characteristics for the PS in Variable Phase Mode**

Symbol	Description			Units
Phase Shifting Range				
MAX_STEPS(2)	Maximum allowed number of DCM_DELAY_STEP steps for a given CLKIN clock period, where T = CLKIN clock period in ns. If using CLKIN_DIVIDE_BY_2 = TRUE, double the clock effective clock period.	CLKIN < 60 MHz	±[INTEGER(10 • (T_{CLKIN} – 3 ns))]	steps
		CLKIN ≥ 60 MHz	±[INTEGER(15 • (T_{CLKIN} – 3 ns))]	steps
FINE_SHIFT_RANGE_MIN	Minimum guaranteed delay for variable phase shifting	±[MAX_STEPS • DCM_DELAY_STEP_MIN]		ns
FINE_SHIFT_RANGE_MAX	Maximum guaranteed delay for variable phase shifting	±[MAX_STEPS • DCM_DELAY_STEP_MAX]		ns

Notes:
1. The numbers in this table are based on the operating conditions set forth in Table 6 and Table 30.
2. The maximum variable phase shift range, MAX_STEPS, is only valid when the DCM is has no initial fixed phase shifting, i.e., the PHASE_SHIFT attribute is set to 0.
3. The DCM_DELAY_STEP values are provided at the bottom of Table 27.

Miscellaneous DCM Timing

Table 32: **Miscellaneous DCM Timing**

Symbol	Description	Min	Max	Units
DCM_RST_PW_MIN(1)	Minimum duration of a RST pulse width	3	-	CLKIN cycles
DCM_RST_PW_MAX(2)	Maximum duration of a RST pulse width	N/A	N/A	seconds
		N/A	N/A	seconds
DCM_CONFIG_LAG_TIME(3)	Maximum duration from V_{CCINT} applied to FPGA configuration successfully completed (DONE pin goes High) and clocks applied to DCM DLL	N/A	N/A	minutes
		N/A	N/A	minutes

Notes:
1. This limit only applies to applications that use the DCM DLL outputs (CLK0, CLK90, CLK180, CLK270, CLK2X, CLK2X180, and CLKDV). The DCM DFS outputs (CLKFX, CLKFX180) are unaffected.
2. This specification is equivalent to the Virtex-4 DCM_RESET specification. This specification does not apply for Spartan-3E FPGAs.
3. This specification is equivalent to the Virtex-4 TCONFIG specification. This specification does not apply for Spartan-3E FPGAs.

Configuration and JTAG Timing

Table 33: **Power-On Timing and the Beginning of Configuration**

Symbol	Description	Device	-4 Speed Grade		Units
			Min	Max	
T_{POR}(2)	The time from the application of V_{CCINT}, V_{CCAUX}, and V_{CCO} Bank 2 supply voltage ramps (whichever occurs last) to the rising transition of the INIT_B pin	XA3S100E	-	5	ms
		XA3S250E	-	5	ms
		XA3S500E	-	5	ms
		XA3S1200E	-	5	ms
		XA3S1600E	-	7	ms
T_{PROG}	The width of the low-going pulse on the PROG_B pin	All	0.5	-	µs
T_{PL}(2)	The time from the rising edge of the PROG_B pin to the rising transition on the INIT_B pin	XA3S100E	-	0.5	ms
		XA3S250E	-	0.5	ms
		XA3S500E	-	1	ms
		XA3S1200E	-	2	ms
		XA3S1600E	-	2	ms
T_{INIT}	Minimum Low pulse width on INIT_B output	All	250	-	ns
T_{ICCK}(3)	The time from the rising edge of the INIT_B pin to the generation of the configuration clock signal at the CCLK output pin	All	0.5	4.0	µs

Notes:

1. The numbers in this table are based on the operating conditions set forth in Table 6. This means power must be applied to all V_{CCINT}, V_{CCO}, and V_{CCAUX} lines.
2. Power-on reset and the clearing of configuration memory occurs during this period.
3. This specification applies only to the Master Serial, SPI, BPI-Up, and BPI-Down modes.

Configuration Clock (CCLK) Characteristics

Table 34: **Master Mode CCLK Output Period by *ConfigRate* Option Setting**

Symbol	Description	*ConfigRate* Setting	Temperature Range	Minimum	Maximum	Units
T_{CCLK1}	CCLK clock period by ***ConfigRate*** setting	1 *(power-on value and default value)*	I-Grade Q-Grade	485	1,250	ns
T_{CCLK3}		3	I-Grade Q-Grade	242	625	ns
T_{CCLK6}		6	I-Grade Q-Grade	121	313	ns
T_{CCLK12}		12	I-Grade Q-Grade	60.6	157	ns
T_{CCLK25}		25	I-Grade Q-Grade	30.3	78.2	ns
T_{CCLK50}		50	I-Grade Q-Grade	15.1	39.1	ns

Notes:

1. Set the ***ConfigRate*** option value when generating a configuration bitstream. See Bitstream Generator (BitGen) Options in DS312, Module 2.

Table 35: **Master Mode CCLK Output Frequency by *ConfigRate* Option Setting**

Symbol	Description	*ConfigRate* Setting	Temperature Range	Minimum	Maximum	Units
F_{CCLK1}	Equivalent CCLK clock frequency by ***ConfigRate*** setting	1 *(power-on value and default value)*	I-Grade Q-Grade	0.8	2.1	MHz
F_{CCLK3}		3	I-Grade Q-Grade	1.6	4.2	MHz
F_{CCLK6}		6	I-Grade Q-Grade	3.2	8.3	MHz
F_{CCLK12}		12	I-Grade Q-Grade	6.4	16.5	MHz
F_{CCLK25}		25	I-Grade Q-Grade	12.8	33.0	MHz
F_{CCLK50}		50	I-Grade Q-Grade	25.6	66.0	MHz

Table 36: **Master Mode CCLK Output Minimum Low and High Time**

Symbol	Description		*ConfigRate* Setting						Units
			1	3	6	12	25	50	
T_{MCCL}, T_{MCCH}	Master mode CCLK minimum Low and High time	I-Grade Q-Grade	235	117	58	29.3	14.5	7.3	ns

Table 37: **Slave Mode CCLK Input Low and High Time**

Symbol	Description	Min	Max	Units
T_{SCCL}, T_{SCCH}	CCLK Low and High time	5	∞	ns

Master Serial and Slave Serial Mode Timing

Table 38: **Timing for the Master Serial and Slave Serial Configuration Modes**

Symbol	Description		Slave/ Master	-4 Speed Grade		Units
				Min	Max	
Clock-to-Output Times						
T_{CCO}	The time from the falling transition on the CCLK pin to data appearing at the DOUT pin		Both	1.5	10.0	ns
Setup Times						
T_{DCC}	The time from the setup of data at the DIN pin to the active edge of the CCLK pin		Both	11.0	-	ns
Hold Times						
T_{CCD}	The time from the active edge of the CCLK pin to the point when data is last held at the DIN pin		Both	0	-	ns
Clock Timing						
T_{CCH}	High pulse width at the CCLK input pin		Master	See Table 36		
			Slave	See Table 37		
T_{CCL}	Low pulse width at the CCLK input pin		Master	See Table 36		
			Slave	See Table 37		
F_{CCSER}	Frequency of the clock signal at the CCLK input pin	No bitstream compression	Slave	0	66(2)	MHz
		With bitstream compression		0	20	MHz

Notes:

1. The numbers in this table are based on the operating conditions set forth in Table 6.
2. For serial configuration with a daisy-chain of multiple FPGAs, the maximum limit is 25 MHz.

Slave Parallel Mode Timing

Table 39: **Timing for the Slave Parallel Configuration Mode**

Symbol	Description			-4 Speed Grade		Units
				Min	Max	
Clock-to-Output Times						
T_{SMCKBY}	The time from the rising transition on the CCLK pin to a signal transition at the BUSY pin			-	12.0	ns
Setup Times						
T_{SMDCC}	The time from the setup of data at the D0-D7 pins to the active edge the CCLK pin			11.0	-	ns
T_{SMCSCC}	Setup time on the CSI_B pin before the active edge of the CCLK pin			10.0	-	ns
T_{SMCCW}(2)	Setup time on the RDWR_B pin before active edge of the CCLK pin			23.0	-	ns
Hold Times						
T_{SMCCD}	The time from the active edge of the CCLK pin to the point when data is last held at the D0-D7 pins			1.0	-	ns
T_{SMCCCS}	The time from the active edge of the CCLK pin to the point when a logic level is last held at the CSO_B pin			0	-	ns
T_{SMWCC}	The time from the active edge of the CCLK pin to the point when a logic level is last held at the RDWR_B pin			0	-	ns
Clock Timing						
T_{CCH}	The High pulse width at the CCLK input pin			5	-	ns
T_{CCL}	The Low pulse width at the CCLK input pin			5	-	ns
F_{CCPAR}	Frequency of the clock signal at the CCLK input pin	No bitstream compression	Not using the BUSY pin(2)	0	50	MHz
			Using the BUSY pin	0	66	MHz
		With bitstream compression		0	20	MHz

Notes:

1. The numbers in this table are based on the operating conditions set forth in Table 6.
2. In the Slave Parallel mode, it is necessary to use the BUSY pin when the CCLK frequency exceeds this maximum specification.
3. Some Xilinx documents refer to Parallel modes as “SelectMAP” modes.

Serial Peripheral Interface Configuration Timing

Table 40: **Timing for SPI Configuration Mode**

Symbol	Description	Minimum	Maximum	Units
T_{CCLK1}	Initial CCLK clock period	(see Table 34)		
T_{CCLKn}	CCLK clock period after FPGA loads ConfigRate setting	(see Table 34)		
T_{MINIT}	Setup time on VS[2:0] and M[2:0] mode pins before the rising edge of INIT_B	50	-	ns
T_{INITM}	Hold time on VS[2:0] and M[2:0]mode pins after the rising edge of INIT_B	0	-	ns
T_{CCO}	MOSI output valid after CCLK edge	See Table 38		
T_{DCC}	Setup time on DIN data input before CCLK edge	See Table 38		
T_{CCD}	Hold time on DIN data input after CCLK edge	See Table 38		

Table 41: **Configuration Timing Requirements for Attached SPI Serial Flash**

Symbol	Description	Requirement	Units
T_{CCS}	SPI serial Flash PROM chip-select time	$T_{CCS} \le T_{MCCL1} - T_{CCO}$	ns
T_{DSU}	SPI serial Flash PROM data input setup time	$T_{DSU} \le T_{MCCL1} - T_{CCO}$	ns
T_{DH}	SPI serial Flash PROM data input hold time	$T_{DH} \le T_{MCCH1}$	ns
T_V	SPI serial Flash PROM data clock-to-output time	$T_V \le T_{MCCLn} - T_{DCC}$	ns
f_C or f_R	Maximum SPI serial Flash PROM clock frequency (also depends on specific read command used)	$f_C \ge \frac{1}{T_{CCLKn(min)}}$	MHz

Notes:

1. These requirements are for successful FPGA configuration in SPI mode, where the FPGA provides the CCLK frequency. The post configuration timing can be different to support the specific needs of the application loaded into the FPGA and the resulting clock source.
2. Subtract additional printed circuit board routing delay as required by the application.

Byte Peripheral Interface Configuration Timing

Table 42: **Timing for BPI Configuration Mode**

Symbol	Description		Minimum	Maximum	Units
T_{CCLK1}	Initial CCLK clock period		(see Table 34)		
T_{CCLKn}	CCLK clock period after FPGA loads ConfigRate setting		(see Table 34)		
T_{MINIT}	Setup time on CSI_B, RDWR_B, and M[2:0] mode pins before the rising edge of INIT_B		50	-	ns
T_{INITM}	Hold time on CSI_B, RDWR_B, and M[2:0] mode pins after the rising edge of INIT_B		0	-	ns
$T_{INITADDR}$	Minimum period of initial A[23:0] address cycle; LDC[2:0] and HDC are asserted and valid	**BPI-UP:** (M[2:0]=<0:1:0>)	5	5	T_{CCLK1} cycles
		BPI-DN: (M[2:0]=<0:1:1>)	2	2	
T_{CCO}	Address A[23:0] outputs valid after CCLK falling edge		See Table 38		
T_{DCC}	Setup time on D[7:0] data inputs before CCLK rising edge		See Table 38		
T_{CCD}	Hold time on D[7:0] data inputs after CCLK rising edge		See Table 38		

Table 43: **Configuration Timing Requirements for Attached Parallel NOR Flash**

Symbol	Description	Requirement	Units
T_{CE} (t_{ELQV})	Parallel NOR Flash PROM chip-select time	$T_{CE} \leq T_{INITADDR}$	ns
T_{OE} (t_{GLQV})	Parallel NOR Flash PROM output-enable time	$T_{OE} \leq T_{INITADDR}$	ns
T_{ACC} (t_{AVQV})	Parallel NOR Flash PROM read access time	$T_{ACC} \leq 0.5T_{CCLKn(min)} - T_{CCO} - T_{DCC} - PCB$	ns
T_{BYTE} (t_{FLQV}, t_{FHQV})	For x8/x16 PROMs only: BYTE# to output valid time(3)	$T_{BYTE} \leq T_{INITADDR}$	ns

Notes:

1. These requirements are for successful FPGA configuration in BPI mode, where the FPGA provides the CCLK frequency. The post configuration timing can be different to support the specific needs of the application loaded into the FPGA and the resulting clock source.
2. Subtract additional printed circuit board routing delay as required by the application.
3. The initial BYTE# timing can be extended using an external, appropriately sized pull-down resistor on the FPGA's LDC2 pin. The resistor value also depends on whether the FPGA's HSWAP pin is High or Low.

IEEE 1149.1/1553 JTAG Test Access Port Timing

Table 44: **Timing for the JTAG Test Access Port**

Symbol	Description	-4 Speed Grade		Units
		Min	Max	
Clock-to-Output Times				
T_{TCKTDO}	The time from the falling transition on the TCK pin to data appearing at the TDO pin	1.0	11.0	ns
Setup Times				
T_{TDITCK}	The time from the setup of data at the TDI pin to the rising transition at the TCK pin	7.0	-	ns
T_{TMSTCK}	The time from the setup of a logic level at the TMS pin to the rising transition at the TCK pin	7.0	-	ns
Hold Times				
T_{TCKTDI}	The time from the rising transition at the TCK pin to the point when data is last held at the TDI pin	0	-	ns
T_{TCKTMS}	The time from the rising transition at the TCK pin to the point when a logic level is last held at the TMS pin	0	-	ns
Clock Timing				
T_{CCH}	The High pulse width at the TCK pin	5	-	ns
T_{CCL}	The Low pulse width at the TCK pin	5	-	ns
F_{TCK}	Frequency of the TCK signal	-	25	MHz

Notes:

1. The numbers in this table are based on the operating conditions set forth in Table 6.